WHAT IS CLAIMED IS:

1.   A photomask comprising:

a transparent substrate;

a plurality of light-shielding patterns aligned over the transparent substrate in two dimensions, each of the light-shielding patterns having length and width measurements that differ from each other; and

at least one through hole penetrating a predetermined region of each of the light-shielding patterns to expose the transparent substrate.

2.   The photomask according to claim 1, wherein the plurality of light-shielding patterns, aligned in two dimensions, have equal length and width measurements.

3.   The photomask according to claim 2, wherein longitudinal axes of the light-shielding patterns having equal length and width measurements are in parallel.

4.   The photomask according to claim 3, wherein distances between neighboring light-shielding patterns, aligned in an extension line in each of the longitudinal axes of the light-shielding patterns, are smaller than the equal length of the light-shielding patterns.

5.   The photomask according to claim 1, wherein a first longitudinal pitch of the light-shielding patterns is at least twice as long as a short pitch of the light-shielding patterns in a short axes, wherein the first longitudinal pitch is the distance from one center point between a pair of light shielding patterns to another center point between a neighboring pair of light shielding patterns in each of the longitudinal axes, , and the short pitch is the distance between center points of neighboring light-shielding patterns in the short axes.

6.   The photomask according to claim 1, wherein a width of the at least one through hole penetrating each of the light-shielding patterns is less than 3/4 the width of the light-shielding pattern penetrated by the through hole.

7.   The photomask according to claim 1, wherein the at least one through hole is located to evenly divide a first longitudinal pitch of the light-shielding pattern, such that a length of a second pitch is proximate to that of a short pitch in a short axes, wherein the first longitudinal pitch is the distance from one center point between a pair of light shielding patterns to another center point between a neighboring pair of light shielding patterns in a longitudinal axes, the second pitch is the length of divided parts of the first longitudinal pitch, and the short pitch is the distance between center points of neighboring light-shielding patterns in the short axes.

8.   The photomask according to claim 7, wherein the short pitch is equal to the second pitch.

9.   A method of fabricating a photomask comprising the steps of:

a) forming a light-shielding layer over a transparent substrate;

b) patterning the light-shielding layer to form a plurality of light-shielding patterns, which are repeatedly aligned in two dimensions on the transparent substrate, each of the light-shielding patterns having length and width measurements that differ from each other; and

c) forming at least one through hole penetrating a predetermined region of each of the light-shielding patterns to expose the transparent substrate.

10.   The method of fabricating a photomask according to claim 9, wherein the plurality of light-shielding patterns, aligned in two dimensions, have identical length and width measurements.

11.   The method of fabricating a photomask according to claim 10, wherein longitudinal axes of the light-shielding patterns, having identical length and width measurements, are in parallel.

12.   The method of claim 9, wherein the step of forming at least one through hole comprises forming at least one through hole having a width less than 3/4 the width of the light-shielding pattern penetrated by the through hole.

13.   The method of claim 9, wherein the step of forming at least one through hole comprises locating the at least one through hole to evenly divide a first longitudinal pitch of the light-shielding pattern, such that a length of a second pitch is proximate to that of a short pitch in a short axes, wherein the first longitudinal pitch is the distance from one center point between a pair of light shielding patterns to another center point between a neighboring pair of light shielding patterns in a longitudinal axes, the second pitch is the length of divided parts of the first longitudinal pitch, and the short pitch is the distance between center points of neighboring light-shielding patterns in the short axes.

14.   A photomask fabricated by a method comprising:

a) forming a light-shielding layer over a transparent substrate;

b) patterning the light-shielding layer to form a plurality of light-shielding patterns, which are repeatedly aligned in two dimensions on the transparent substrate, each of the light-shielding patterns having length and width measurements that differ from each other; and

c) forming at least one through hole penetrating a predetermined region of each of the light-shielding patterns to expose the transparent substrate.

15.   The photomask according to claim 14, wherein the plurality of light-shielding patterns, aligned in two dimensions, have identical length and width measurements.

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16. The photomask according to claim 15, wherein longitudinal axes of the light-shielding patterns, having identical length and width measurements, are in parallel.

17. The photomask according to claim 14, wherein the step of forming at least one through hole comprises forming at least one through hole having a width less than 3/4 the width of the light-shielding pattern penetrated by the through hole.

18. The photomask according to claim 14, wherein the step of forming at least one through hole comprises locating the at least one through hole to evenly divide a first longitudinal pitch of the light-shielding pattern, such that a length of a second pitch is proximate to that of a short pitch in a short axes, wherein the first longitudinal pitch is the distance from one center point between a pair of light shielding patterns to another center point between a neighboring pair of light shielding patterns in a longitudinal axes, the second pitch is the length of divided parts of the first longitudinal pitch, and the short pitch is the distance between center points of neighboring light-shielding patterns in the short axes.